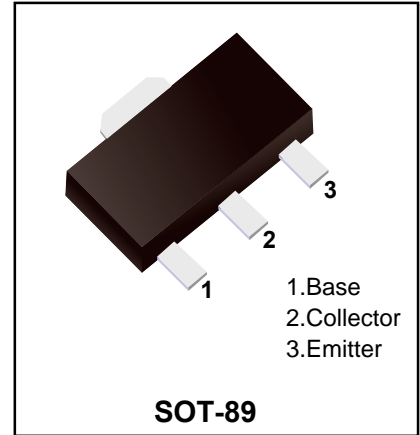


**PNP Transistors**



**Features**

- Low  $V_{CE(sat)}$ .  
 $V_{CE(sat)} = -0.5V$  (Typ.)  
 ( $I_C/I_B = -2A / -0.2A$ )

**Absolute Maximum Rating (Ta=25°C)**

Parameter	Symbol	Rating	Unit
Collector-base Voltage	$V_{CB0}$	-40	V
Collector-emitter Voltage	$V_{CE0}$	-32	V
Emitter-base Voltage	$V_{EB0}$	-5	V
Collector current	$I_C$	-2	A
	$I_{CP}^*$	-3	A
Collector power dissipation	$P_C$	0.5	W
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

\* PW=100ms

**Electrical Characteristics (Ta=25°C)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$BV_{CB0}$	$I_C = -50 \mu A$	-40			V
Collector-emitter breakdown voltage	$BV_{CE0}$	$I_C = -1mA$	-32			V
Emitter-base breakdown voltage	$BV_{EB0}$	$I_E = -50 \mu A$	-5			V
Collector cutoff current	$I_{CBO}$	$V_{CB} = -20V$			-1	$\mu A$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -4V$			-1	$\mu A$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -2A, I_B = -0.2A$		-0.5	-0.8	V
DC current transfer ratio	$h_{FE}$	$V_{CE} = -3V, I_C = -0.5A$	82		390	
Output Capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$		50		pF
Transition frequency	$f_T$	$V_{CE} = -5V, I_E = 0.5A, f = 30MHz$		100		MHz

**$h_{FE}$  Classification**

Type	2SB1188-P	2SB1188-Q	2SB1188-R
Range	82-180	120-270	180-390
Marking	BCP*	BCQ*	BCR*

**Typical Characteristics**

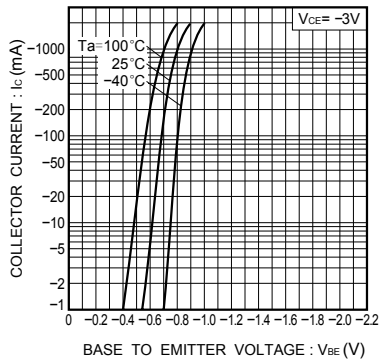


Fig.1 Grounded emitter propagation characteristics

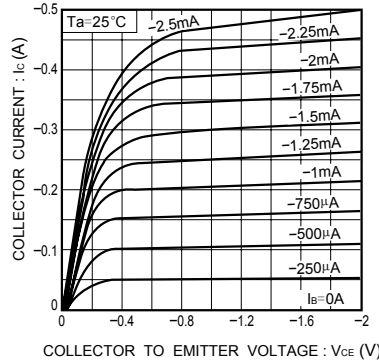


Fig.2 Grounded emitter output characteristics

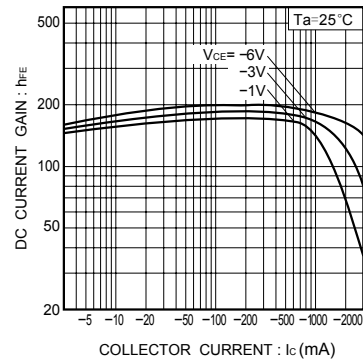


Fig.3 DC current gain vs. collector current ( I )

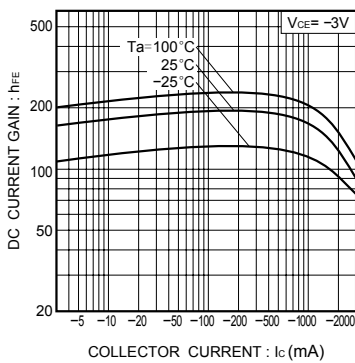


Fig.4 DC current gain vs. collector current (II)

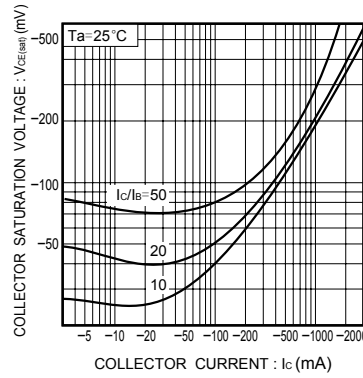


Fig.5 Collector-emitter saturation voltage vs. collector current ( I )

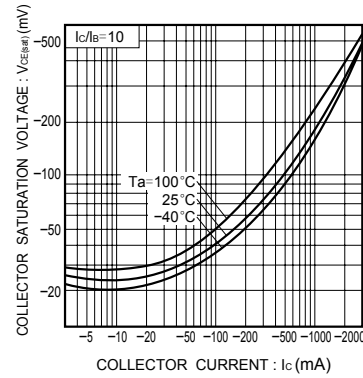


Fig.6 Collector-emitter saturation voltage vs. collector current (II)

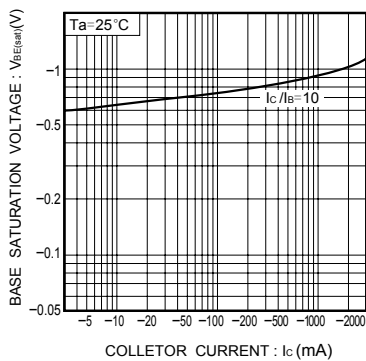


Fig.7 Base-emitter saturation voltage vs. collector current

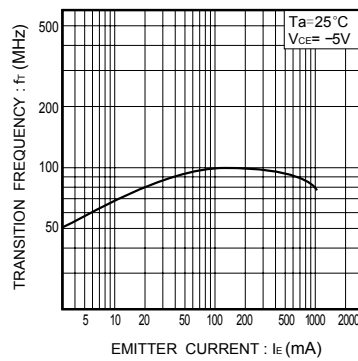


Fig.8 Gain bandwidth product vs. emitter current

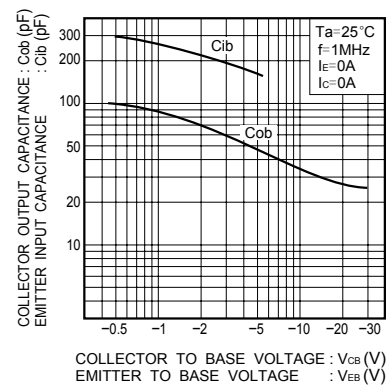


Fig.9 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

Typical Characteristics

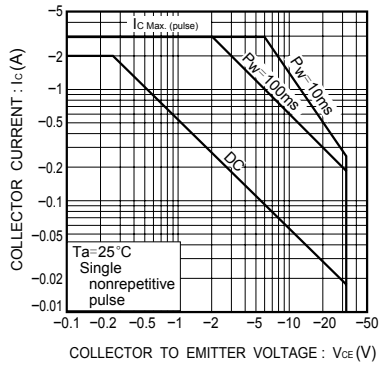


Fig.10 Safe operation area

**Ordering information**

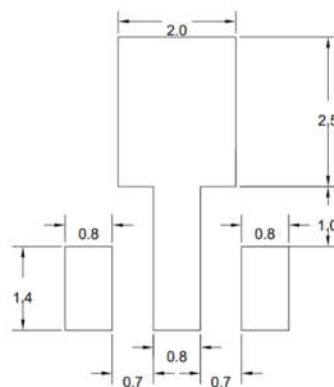
Package	Packing Description	Base Quantity	Packing Quantity
SOT-89	Tape/Reel,7"reel	1000pcs/Reel	6000PCS/Box 30000PCS/Carton

**Package Dimensions**

**SOT-89**

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	1.40	1.60	0.055	0.063
b	0.32	0.52	0.013	0.020
b1	0.38	0.58	0.015	0.023
c	0.35	0.45	0.014	0.018
D	4.40	4.60	0.173	0.181
D1	1.45	1.65	0.057	0.065
D2	1.70	1.80	0.067	0.071
E	2.30	2.60	0.091	0.102
E1	3.95	4.25	0.156	0.167
E2	1.80	2.00	0.071	0.079
e	1.40	1.60	0.055	0.063
e1	2.80	3.20	0.110	0.126
L	0.90	1.20	0.035	0.047

**The recommended mounting pad size**



UNIT:MM

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